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# 1SS165

Silicon Schottky Barrier Diode for CATV Balanced Mixer

# HITACHI

ADE-208-397 (Z)  
Rev. 0

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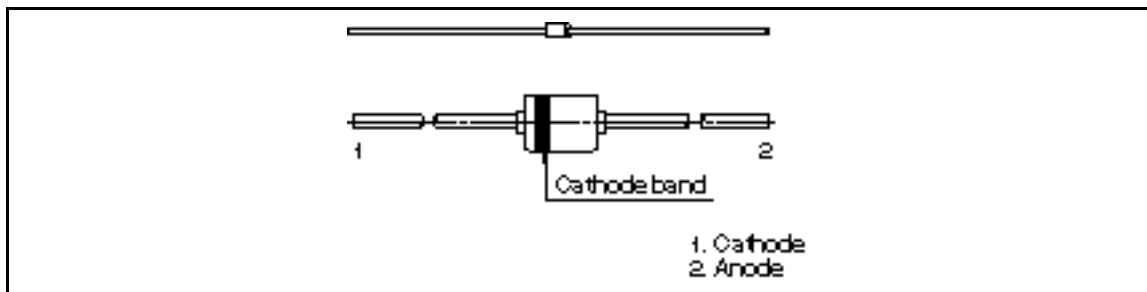
## Features

- Σ Low capacitance. (C = 1.0pF max)
- Σ Small glass package (MHD) enables easy mounting and high reliability.

## Ordering Information

| Type No. | Cathode band | Package Code |
|----------|--------------|--------------|
| 1SS165   | Green        | MHD          |

## Outline



## Absolute Maximum Ratings (Ta = 25°C)

| Item                    | Symbol    | Value       | Unit |
|-------------------------|-----------|-------------|------|
| Reverse voltage         | $V_R$     | 10          | V    |
| Average forward current | $I_O$     | 15          | mA   |
| Peak forward current    | $I_{FM}$  | 35          | mA   |
| Power dissipation       | $P_d$     | 150         | mW   |
| Junction temperature    | $T_j$     | 100         | °C   |
| Storage temperature     | $T_{stg}$ | -55 to +100 | °C   |

## Electrical Characteristics (Ta = 25°C)

| Item                      | Symbol    | Min | Typ | Max | Unit          | Test Condition                                           |
|---------------------------|-----------|-----|-----|-----|---------------|----------------------------------------------------------|
| Forward voltage           | $V_{F1}$  | 365 | —   | 430 | mV            | $I_F = 1\text{mA}$                                       |
|                           | $V_{F2}$  | 520 | —   | 600 |               | $I_F = 10\text{mA}$                                      |
| Reverse current           | $I_{R1}$  | —   | —   | 0.2 | $\mu\text{A}$ | $V_R = 2\text{V}$                                        |
|                           | $I_{R2}$  | —   | —   | 10  |               | $V_R = 10\text{V}$                                       |
| Capacitance               | C         | —   | —   | 1.0 | pF            | $V_R = 0\text{V}$ , $f = 1\text{MHz}$                    |
| Capacitance deviation     | DC        | —   | —   | 0.1 | pF            | $V_R = 0\text{V}$ , $f = 1\text{MHz}$                    |
| Forward voltage deviation | $DV_{F1}$ | —   | —   | 10  | mV            | $I_F = 2.5\text{mA}$                                     |
|                           | $DV_{F2}$ | —   | —   | 10  |               | $I_F = 10\text{mA}$                                      |
| ESD-Capability            | —         | 30  | —   | —   | V             | *1C = 200pF, Both forward and reverse direction 1 pulse. |

- Notes: 1. Failure criterion;  $I_R \geq 50\mu\text{A}$   
2. Each group shall unify a multiple of 4 diodes

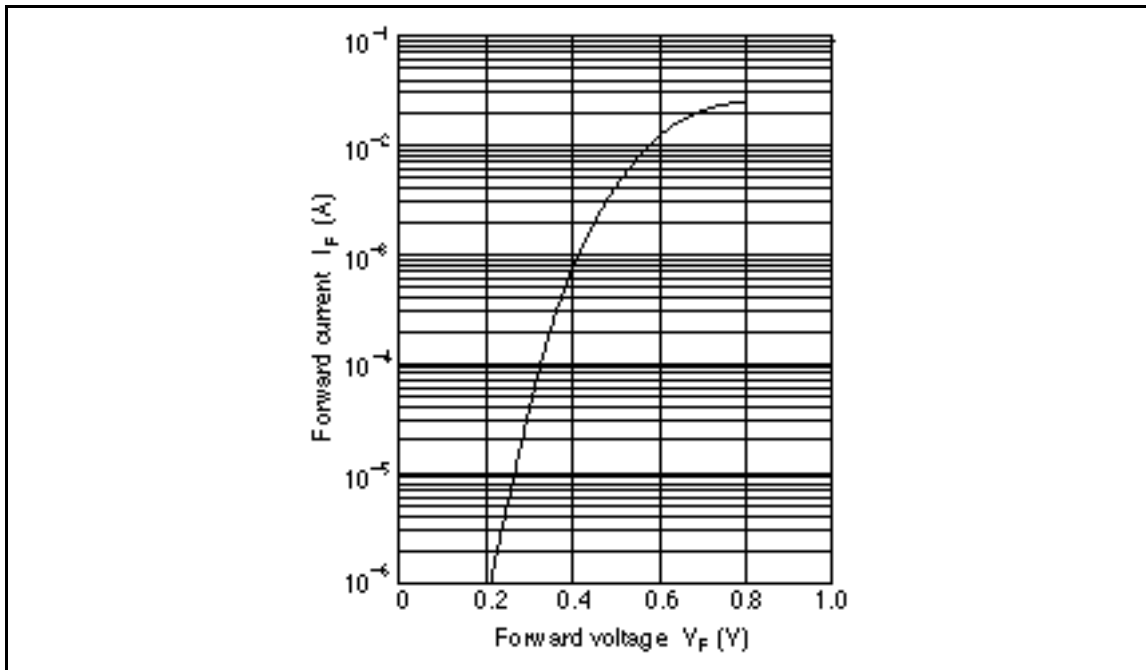


Fig.1 Forward current Vs. Forward voltage

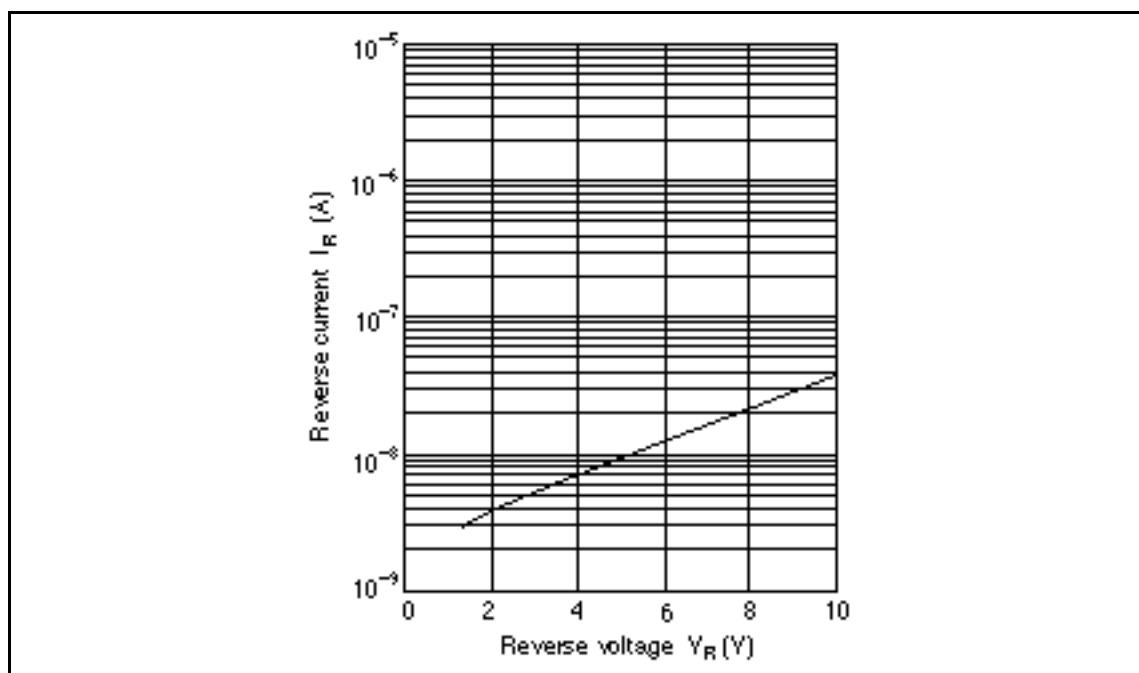


Fig.2 Reverse current Vs. Reverse voltage

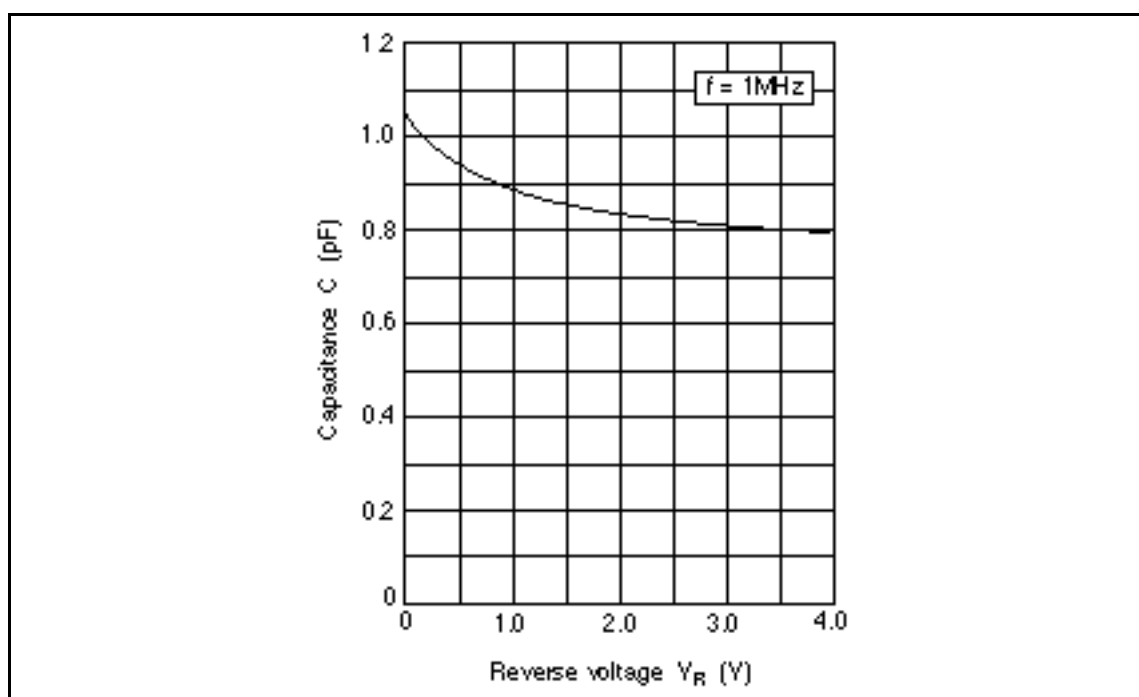


Fig.3 Capacitance Vs. Reverse voltage

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### Package Dimensions

